METHOD FOR FORMING A SEMICONDUCTOR DEVICE

Abstract

First and second dummy structures (201 and 202) are formed over a semiconductor device substrate (10). In one embodiment, portions of the first dummy structure (201) are removed and replaced with a first conductive material (64) to form a first gate electrode (71) and portions of second dummy structure (202) are removed and replaced with a second conductive material (84) to form a second gate electrode (91). In an alternate embodiment, the dummy structures (201 and 202) are formed using a first conductive material (164) that is used to form the first electrode (71). The second electrode is then formed by removing the first conductive material (164) from dummy structures (202) and replacing it with a second conductive material (84). In accordance with embodiments of the present invention, the first conductive material and the second conductive material are different conductive materials.

Fig's. 3, 6 and 8 to accompany abstract.

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